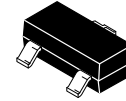


# NPN Darlington Transistor

## BCV27



SOT-23  
CASE 318

### Description

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from process 05.

### ABSOLUTE MAXIMUM RATINGS

( $T_A = 25^\circ\text{C}$  unless otherwise noted.) (Notes 1, 2)

Symbol	Parameter	Value	Unit
$V_{CEO}$	Collector–Emitter Voltage	30	V
$V_{CBO}$	Collector–Base Voltage	40	V
$V_{EBO}$	Emitter–Base Voltage	10	V
$I_C$	Collector Current – Continuous	1.2	A
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

### THERMAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted.) (Note 3)

Symbol	Parameter	Max	Unit
$P_D$	Total Device Dissipation	350	mW
	Derate Above $25^\circ\text{C}$	2.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$

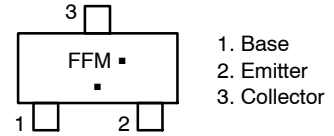
- PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CEO}$	Collector–Emitter Breakdown Voltage	$I_C = 10\text{ mA}, I_B = 0$	30	–	–	V
$V_{(BR)CBO}$	Collector–Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	40	–	–	V
$V_{(BR)EBO}$	Emitter–Base Breakdown Voltage	$I_E = 100\text{ nA}, I_C = 0$	10	–	–	V
$I_{CBO}$	Collector Cut–Off Current	$V_{CB} = 30\text{ V}, I_E = 0$	–	–	0.1	$\mu\text{A}$
$I_{EBO}$	Emitter Cut–Off Current	$V_{EB} = 10\text{ V}, I_C = 0$	–	–	0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}$	4000	–	–	
		$I_C = 10\text{ mA}, V_{CE} = 5.0\text{ V}$	10000	–	–	
		$I_C = 100\text{ mA}, V_{CE} = 5.0\text{ V}$	20000	–	–	
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage	$I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	–	–	1.0	V
$V_{BE(sat)}$	Base–Emitter Saturation Voltage	$I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	–	–	1.5	V
$f_T$	Current Gain – Bandwidth Product	$I_C = 30\text{ mA}, V_{CE} = 5.0\text{ V}, f = 100\text{ MHz}$	–	220	–	MHz
$C_C$	Collector Capacitance	$V_{CB} = 30\text{ V}, I_E = 0, f = 1.0\text{ MHz}$	–	3.5	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### MARKING DIAGRAM



FF = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping
BCV27	SOT-23 (Pb-Free, Halide Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

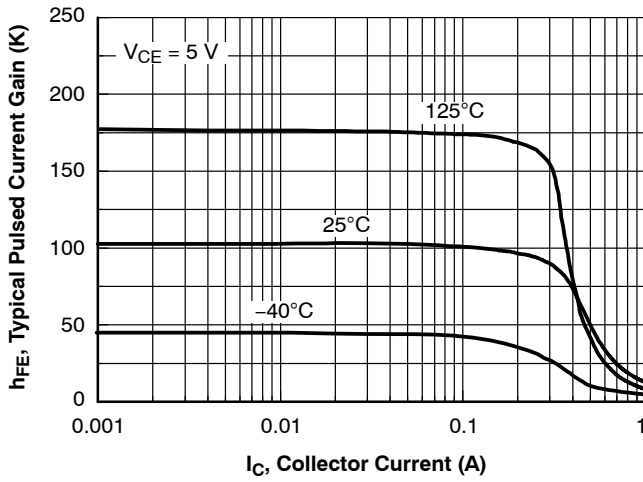


Figure 1. Typical Pulsed Current Gain vs. Collector Current

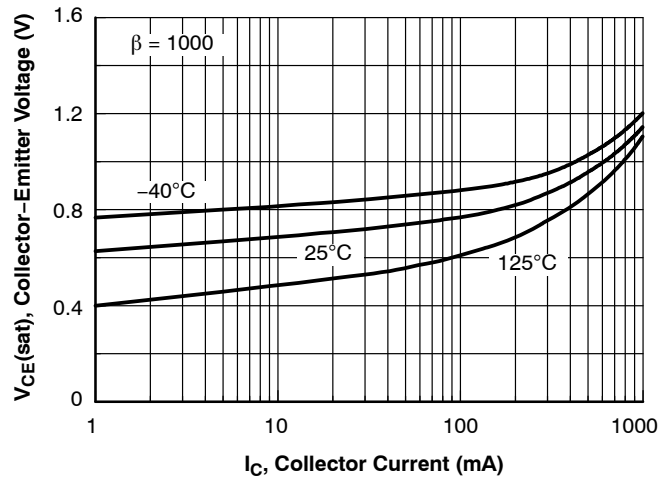


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

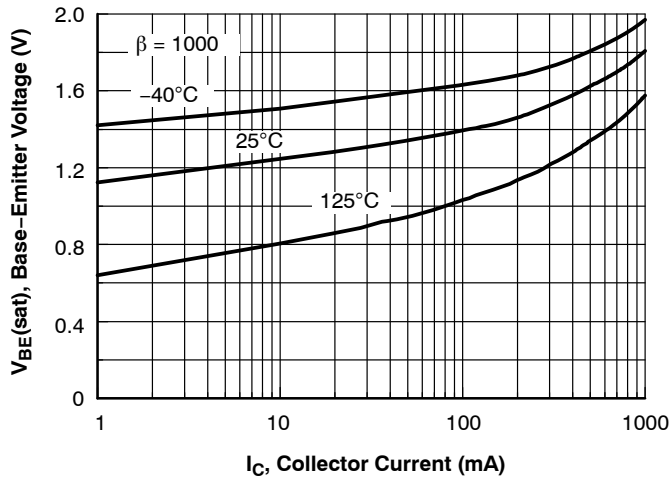


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

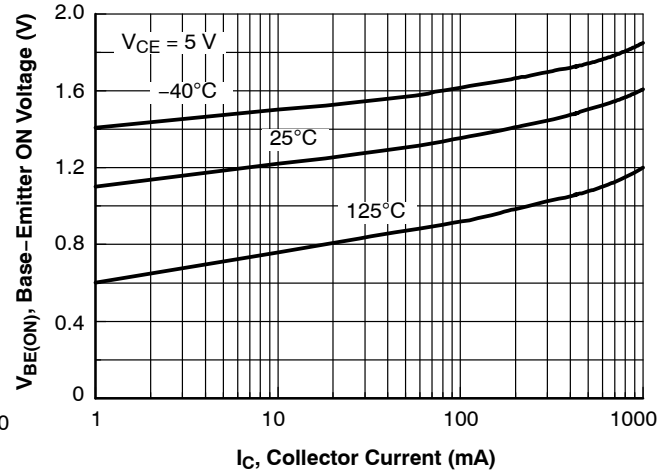


Figure 4. Base Emitter On Voltage vs. Collector Current

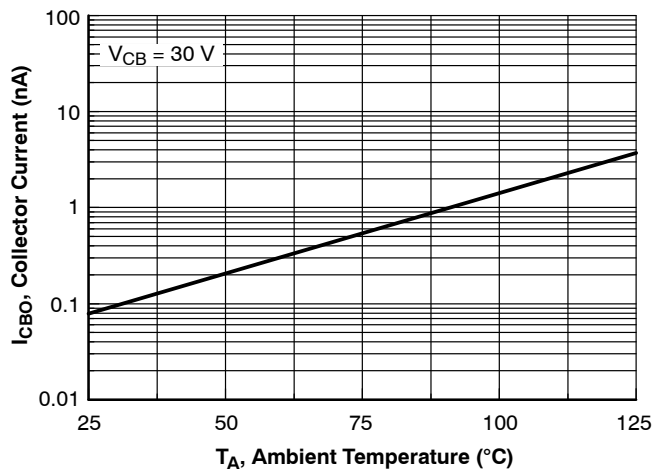


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

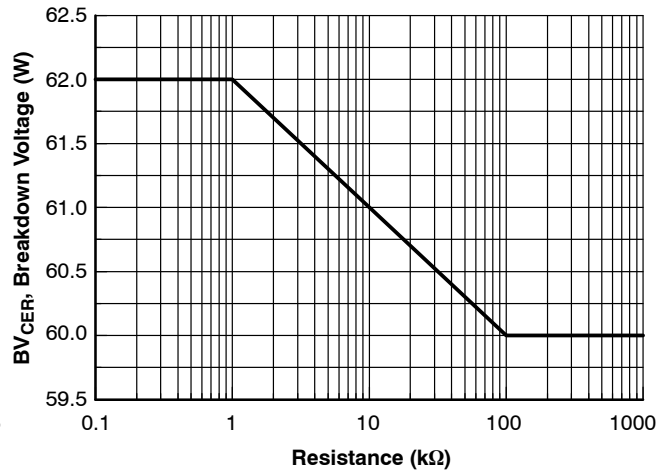


Figure 6. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

# BCV27

## TYPICAL CHARACTERISTICS (Continued)

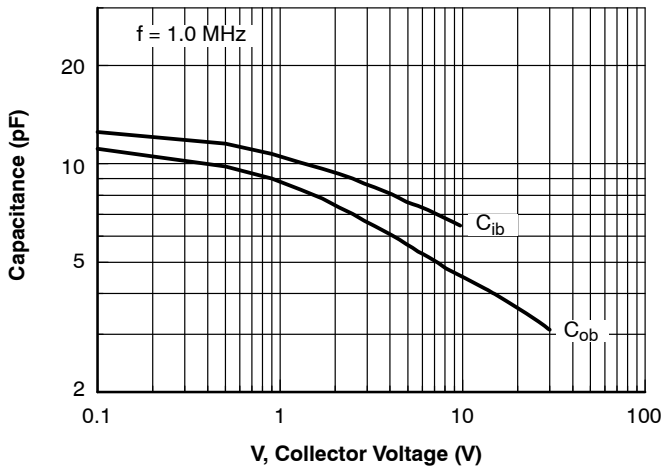


Figure 7. Input and Output Capacitance vs. Reverse Voltage

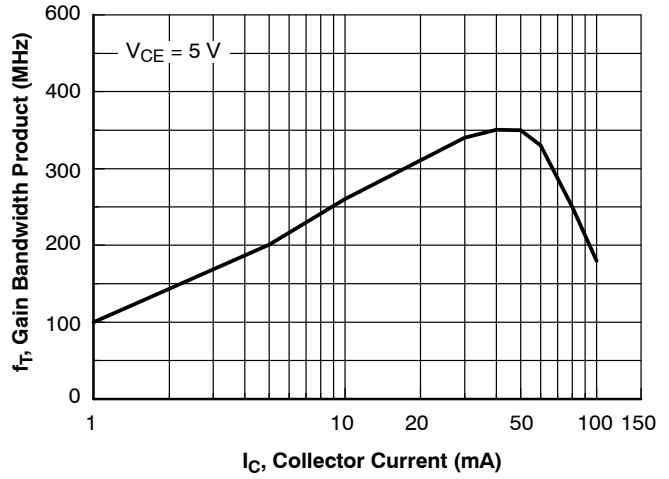


Figure 8. Gain Bandwidth Product vs. Collector Current

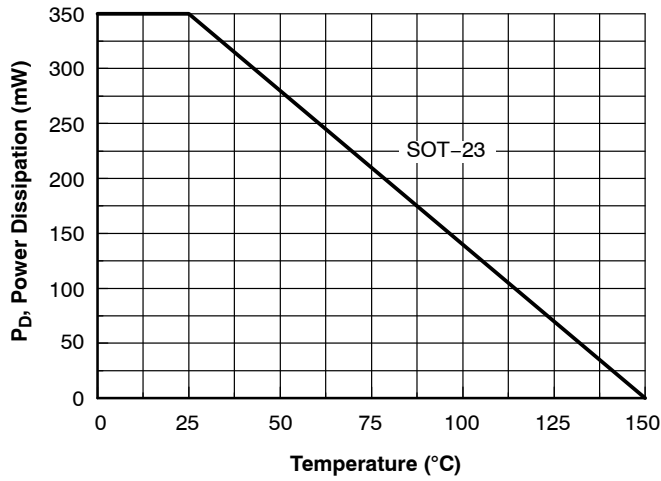
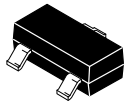


Figure 9. Power Dissipation vs. Ambient Temperature

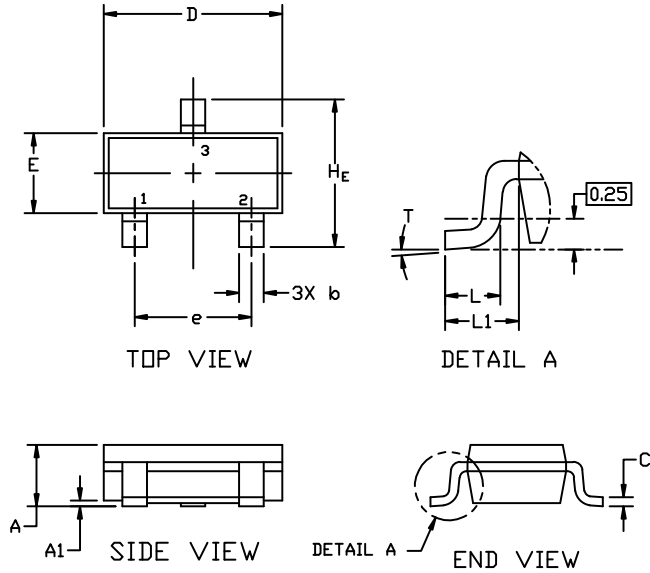
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**SOT-23 (TO-236)**  
CASE 318  
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1

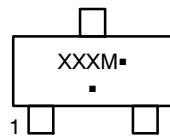


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

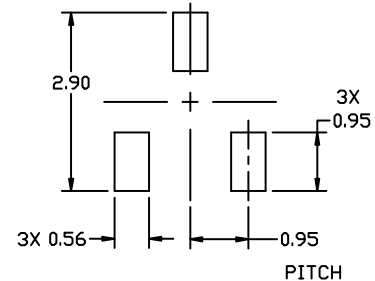
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS



### SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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